

# HiPerFRED

 $V_{RRM}$ 600 V

30 A

30 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Parallel legs

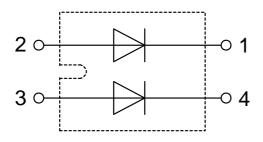
Part number

**DSEP2x31-06B** 



Backside: isolated

**F1** E72873



## Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## **Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper
- internally DCB isolated
- Advanced power cycling

#### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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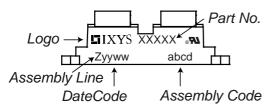


Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			600	V
V <sub>RRM</sub>	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			600	V
I <sub>R</sub>	reverse current, drain current	$V_R = 600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			250	μΑ
		$V_R = 600 V$	$T_{VJ} = 150$ °C			2	mΑ
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 30 A	$T_{VJ} = 25^{\circ}C$			2.49	V
		$I_F = 60 A$				3.16	V
		I <sub>F</sub> = 30 A	T <sub>VJ</sub> = 150°C			1.59	V
		$I_F = 60 \text{ A}$				2.20	V
I <sub>FAV</sub>	average forward current	T <sub>c</sub> = 75°C	T <sub>VJ</sub> = 150°C			30	Α
		rectangular d = 0.5					
V <sub>F0</sub>	threshold voltage	and a decident and a	T <sub>VJ</sub> = 150°C			1.01	V
$\mathbf{r}_{F}$	slope resistance	s calculation only				19.2	mΩ
R <sub>thJC</sub>	thermal resistance junction to case	9				1.15	K/W
R <sub>thCH</sub>	thermal resistance case to heatsin	ık			0.10		K/W
P <sub>tot</sub>	total power dissipation		$T_C = 25^{\circ}C$			100	W
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			250	Α
<b>C</b> <sub>J</sub>	junction capacitance	$V_R = 400 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		26		pF
I <sub>RM</sub>	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		7.5		Α
		$I_F = 30 \text{ A}; V_R = 300 \text{ V}$	$T_{VJ} = 100 ^{\circ}\text{C}$		12.5		Α
t <sub>rr</sub>	reverse recovery time	$\begin{cases} I_F = 30 \text{ A}; V_R = 300 \text{ V} \\ -di_F /dt = 400 \text{ A/µs} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		20		ns
	J	1	$T_{VJ} = 100^{\circ}C$		70		ns



Package SOT-227B (minibloc)			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal					100	Α
T <sub>VJ</sub>	virtual junction temperature				-40		150	°C
Top	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature				-40		150	°C
Weight						30		g
M <sub>D</sub>	mounting torque				1.1		1.5	Nm
$\mathbf{M}_{_{\mathbf{T}}}$	terminal torque				1.1		1.5	Nm
d <sub>Spp/App</sub>	oroonogo diatanoo on ourfa	ce   striking distance through air	terminal to terminal 10.5 terminal to backside 8.6		3.2			mm
d <sub>Spb/Apb</sub>	creepage distance on sunat	ce   striking distance through an			6.8			mm
V <sub>ISOL</sub>	isolation voltage	t = 1 second			3000			V
.002	t = 1 minute		50/60 Hz, RMS; I <sub>ISOL</sub> ≤ 1 mA		2500			V

# **Product Marking**



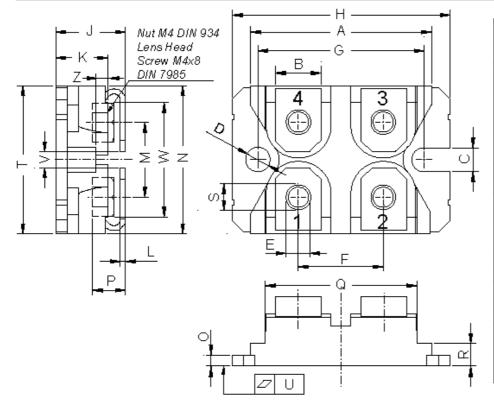
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP2x31-06B	DSEP2x31-06B	Tube	10	476285

Similar Part	Package	Voltage class
DSEP2x31-06A	SOT-227B (minibloc)	600

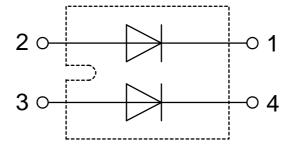
<b>Equivalent Circuits for Simulation</b>			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$	$R_0$	Fast Diode		
V <sub>0 max</sub>	threshold voltage	1.01		V
$R_{0max}$	slope resistance *	17.3		$m\Omega$



## Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
DIM.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Z	2.50	2.70	0.098	0.106	





## **Fast Diode**

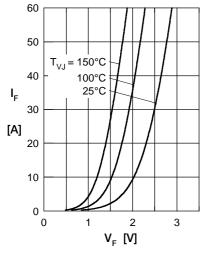


Fig. 1 Forward current I<sub>F</sub> versus V<sub>F</sub>

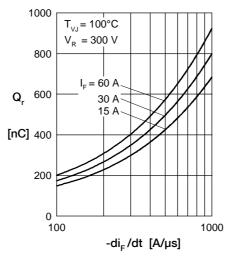


Fig. 2 Reverse recovery charge Q<sub>r</sub> versus -di<sub>F</sub>/dt

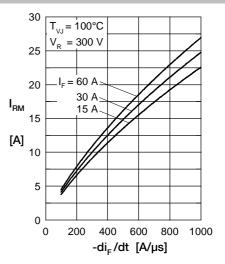


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$ 

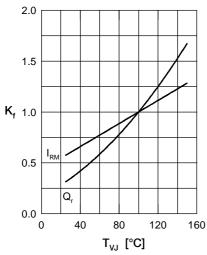


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{V.I}$ 

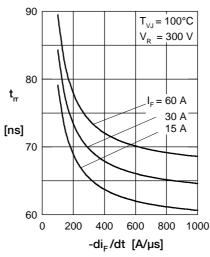


Fig. 5 Recovery time  $t_{rr}$  versus  $-di_{F}/dt$ 

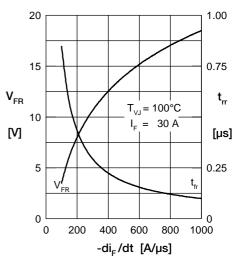


Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_{F}/dt$ 

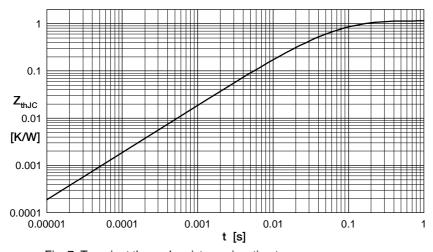


Fig. 7 Transient thermal resistance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	t <sub>i</sub> (s)
1	0.436	0.0055
2	0.482	0.0092
3	0.117	0.0007
4	0.115	0.0418